Chen-Han Chou

List of Publications by Year
in descending order

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15	56	1684188 5	1588992 8
papers	citations	h-index	g-index

16	16	16	100
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Low-Leakage Tetragonal ZrO₂ (EOT < 1 nm) With <italic>In Situ</italic> Plasma Interfacial Passivation on Germanium. IEEE Electron Device Letters, 2016, 37, 138-141.	3.9	13
2	Experimental Realization of Thermal Stability Enhancement of Nickel Germanide Alloy by Using TiN Metal Capping. IEEE Transactions on Electron Devices, 2017, 64, 2314-2320.	3.0	8
3	Improving Thermal Stability and Interface State Density of High- $kappa $ Stacks by Incorporating Hf into an Interfacial Layer on p-Germanium. IEEE Electron Device Letters, 2016, 37, 1379-1382.	3.9	7
4	Incorporating Yttrium into a GeO Interfacial Layer with HfO₂-Based Gate Stack on Ge. ECS Journal of Solid State Science and Technology, 2018, 7, N15-N19.	1.8	6
5	Fabricating a n+-Ge contact with ultralow specific contact resistivity by introducing a PtGe alloy as a contact metal. Applied Physics Letters, 2015, 107, 113503.	3.3	5
6	Demonstration of HfO2-Based Gate Dielectric With Low Interface State Density and Sub-nm EOT on Ge by Incorporating Ti Into Interfacial Layer. IEEE Electron Device Letters, 2019, 40, 174-176.	3.9	5
7	Experimental Realization of a Ternary-Phase Alloy Through Microwave-Activated Annealing for Ge Schottky pMOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 2714-2721.	3.0	4
8	3D-TCAD simulation study of the contact all around T-FinFET structure for 10nm metal-oxide-semiconductor field-effect transistor. , 2016, , .		3
9	Phase-separation phenomenon of NiGePt alloy on n-Ge by microwave annealing. Journal of Alloys and Compounds, 2018, 743, 262-267.	5.5	2
10	Integration of hetero-structure body-tied Ge FinFET using retrograde-well implantation. , 2016, , .		1
11	Integration of microwave-annealed oxidation on germanium metal-oxide-semiconductor devices. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 051204.	1.2	1
12	Comparison of the Physical and Electrical Properties of HfO2/Al2O3/HfO2/GeOx/Ge and HfO2/Al2O3/GeOx/Ge Gate Stacks. Journal of Nanoscience and Nanotechnology, 2019, 19, 4529-4534.	0.9	1
13	High performance Ge Schottky PMOSFETs with ternary-phase alloy. , 2016, , .		0
14	First Experimental Demonstration and Mechanism of Abnormal Palladium Diffusion Induced by Excess Interstitial Ge. IEEE Electron Device Letters, 2018, 39, 1632-1635.	3.9	0
15	Improving Interface State Density of TiN/HfO₂/IL Gate Stack on Si_{0.5} Ge_{0.5} by Optimization of Post Metallization Annealing and Oxygen Pressure. , 2020, , .		0